Elektronische Bauelemente

SSPR33N06S-C

33A, 60V, $R_{DS(ON)}$ 11.5mΩ

N-Channel Enhancement Mode Power MOSFET

RoHS Compliant Product

A suffix of "-C" specifies halogen & lead-free

DESCRIPTION

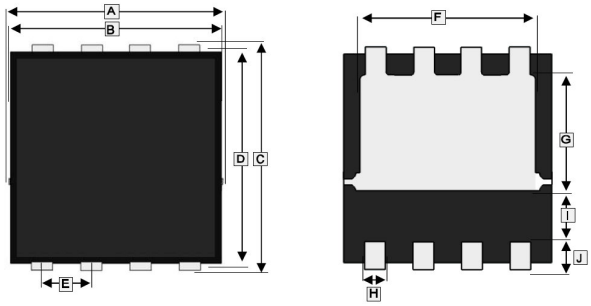
The SSPR33N06S-C is the highest performance trench N-Ch MOSFETs with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The SSPR33N06S-C meet the RoHS and Green Product requirement with full function reliability approved.

FEATURES

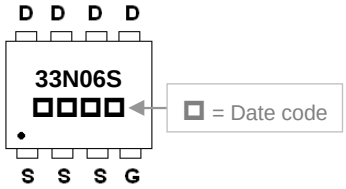
- Advanced High Cell Density Trench Technology
- Super Low Gate Charge
- Green Device Available

SPR-8PP



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	3.00	3.40	G	1.35	1.98
B	3.00	3.25	H	0.24	0.35
C	3.20	3.45	I	0.35 TYP.	
D	3.00	3.20	J	0.60 TYP.	
E	0.65 BSC.		K	0.10	0.25
F	2.39	2.60	L	0.70	0.90

MARKING

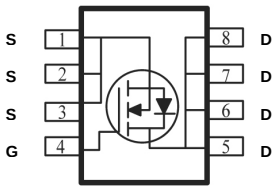


PACKAGE INFORMATION

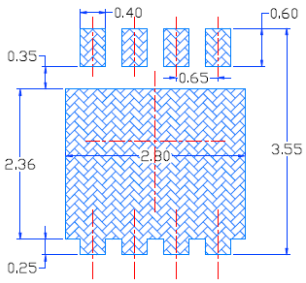
Package	MPQ	Leader Size
SPR-8PP	3K	13 inch

ORDER INFORMATION

Part Number	Type
SSPR33N06S-C	Lead (Pb)-free and Halogen-free



Mounting Pad Layout



*Dimensions in millimeters

ABSOLUTE MAXIMUM RATINGS T_A=25℃ unless otherwise specified)

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [1] (Silicon Limited)	T_C=25℃	I_D	33	A
	T_C=100℃		21	
Continuous Drain Current [1] (Package Limited)	T_C=25℃		26	
Pulsed Drain Current [2 4]		I_{DM}	100	A
Power Dissipation	T_C=25℃	P_D	25	W
Operating Junction & Storage Temperature		T_J, T_{STG}	-55~150	℃
Thermal Resistance Ratings				
Thermal Resistance Junction-Ambient [1]		$R_{\theta JA}$	55	℃/W
Thermal Resistance Junction-Case [1]		$R_{\theta JC}$	5	

ELECTRICAL CHARACTERISTICS (T_J=25℃ unless otherwise specified)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	60	-	-	V	V_{GS}=0V, I_D=250μA
Gate-Threshold Voltage		$V_{GS(th)}$	1	-	2.4	V	V_{DS}=V_{GS}, I_D=250μA
Gate-Source Leakage Current		I_{GSS}	-	-	±100	nA	V_{GS}= ±20V
Drain-Source Leakage Current	T_J=25℃	I_{DSS}	-	-	1	uA	V_{DS}=48V, V_{GS}=0V
	T_J=100℃		-	-	100		V_{DS}=48V, V_{GS}=0V
Static Drain-Source On-Resistance [3]		$R_{DS(ON)}$	-	8.5	11.5	mΩ	V_{GS}=10V, I_D=10A
			-	12	16		V_{GS}=4.5V, I_D=8A
Transconductance		g_{fs}	-	25	-	S	V_{DS}=5V, I_D=10A
Gate Resistance		R_g	-	1.5	-	Ω	V_{DS}=V_{GS}=0V, f=1MHz
Total Gate Charge (4.5V)		Q_g	-	9	-	nC	I_D=10A V_{DD}=30V V_{GS}=10V
Total Gate Charge			-	18.5	-		
Gate-Source Charge		Q_{gs}	-	4.5	-		
Gate-Drain Change		Q_{gd}	-	3.5	-		
Turn-on Delay Time		$T_{d(on)}$	-	6	-	nS	V_{DD}=30V I_D=10A V_{GS}=10V R_G=10Ω
Rise Time		T_r	-	3	-		
Turn-off Delay Time		$T_{d(off)}$	-	25	-		
Fall Time		T_f	-	3	-		
Input Capacitance		C_{iss}	-	1040	-	pF	V_{GS}=0 V_{DS}=30V f=1MHz
Output Capacitance		C_{oss}	-	318	-		
Reverse Transfer Capacitance		C_{rss}	-	15	-		
Source-Drain Diode							
Diode Forward Voltage [3]		V_{SD}	-	-	1.2	V	I_F=10A, V_{GS}=0V
Reverse Recovery Time		T_{rr}	-	25	-	nS	I_F=10A, V_R=30V, dI/dt=300A/μs
Reverse Recovery Charge		Q_{rr}	-	33	-	nC	

Notes:
1. The data tested by surface mounted on a 1 inch^2 FR-4 board with 2oz copper.
2. The Pulse width limited by maximum junction temperature, Pulse Width ≤10μs, Duty Cycle≤2%.
3. The Pulse Test: Pulse Width ≤300μs, Duty Cycle≤2%.
4. Package limit.

CHARACTERISTIC CURVES

Fig 1. Typical Output Characteristics

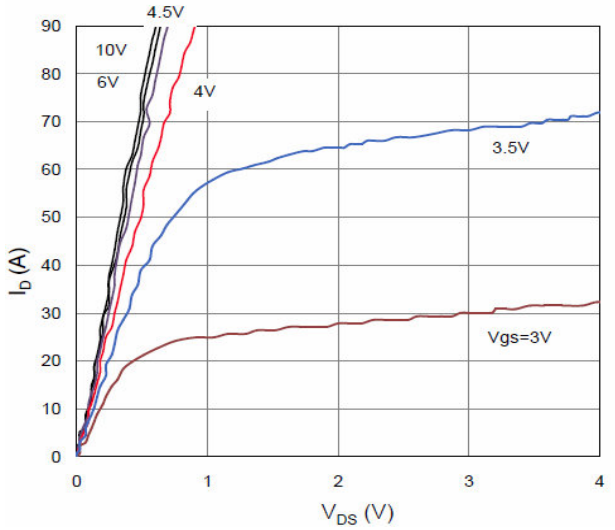


Figure 2. On-Resistance vs. Gate-Source Voltage

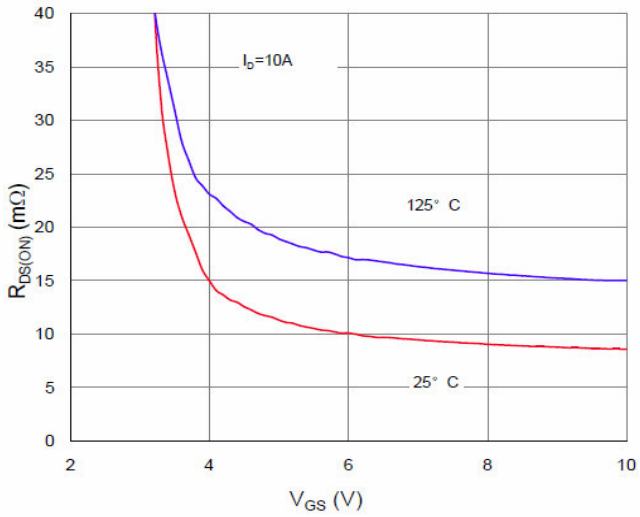


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

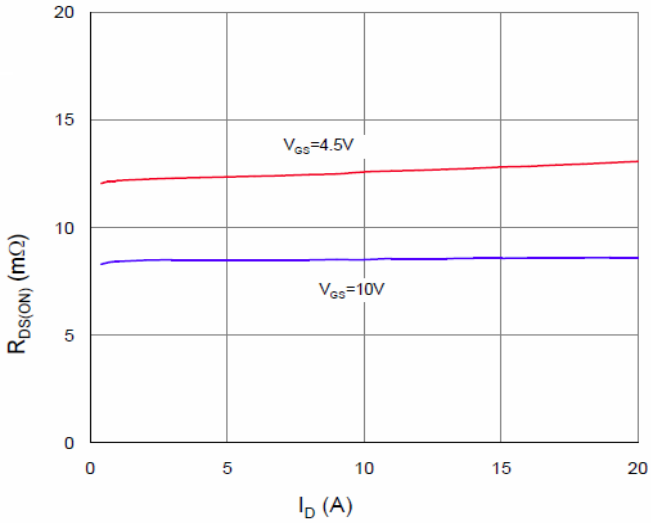


Figure 4. Normalized On-Resistance vs. Junction Temperature

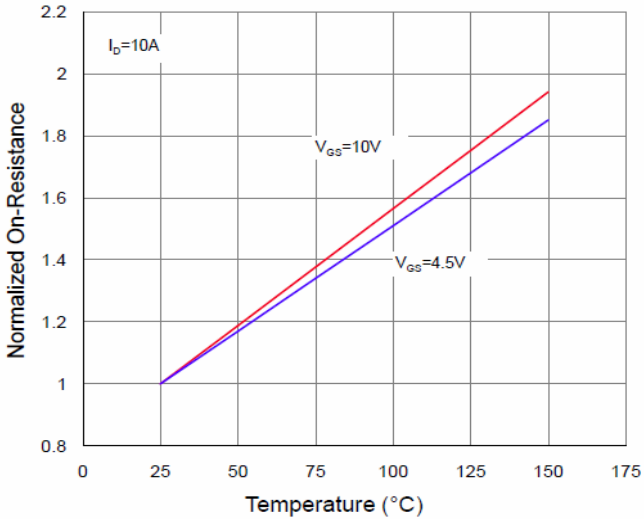


Figure 5. Typical Transfer Characteristics

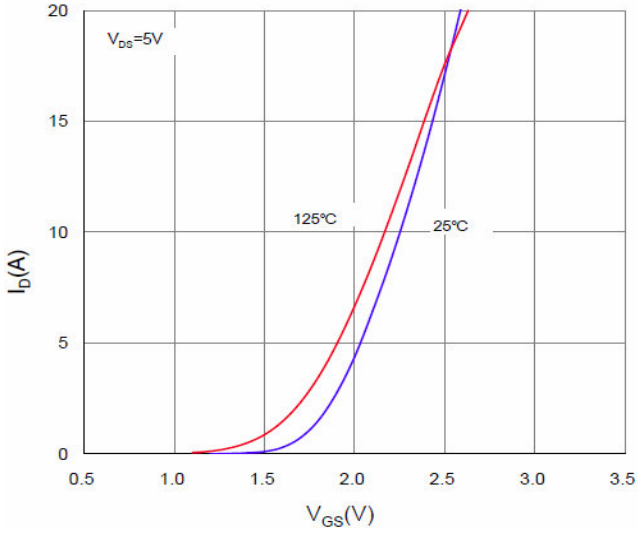
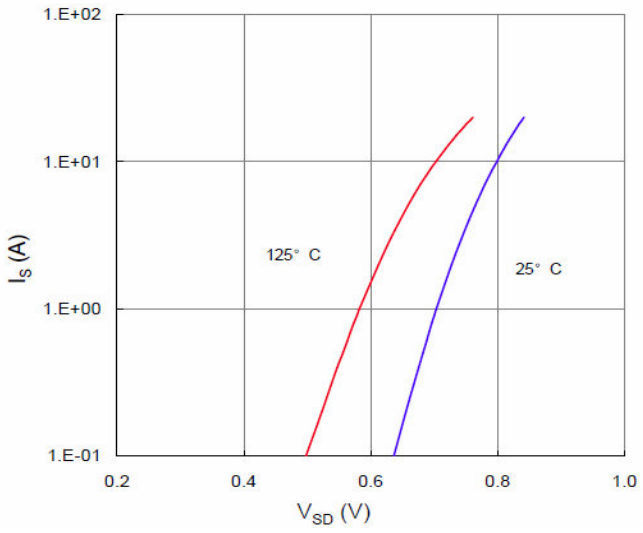


Figure 6. Typical Source-Drain Diode Forward Voltage



CHARACTERISTIC CURVES

Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

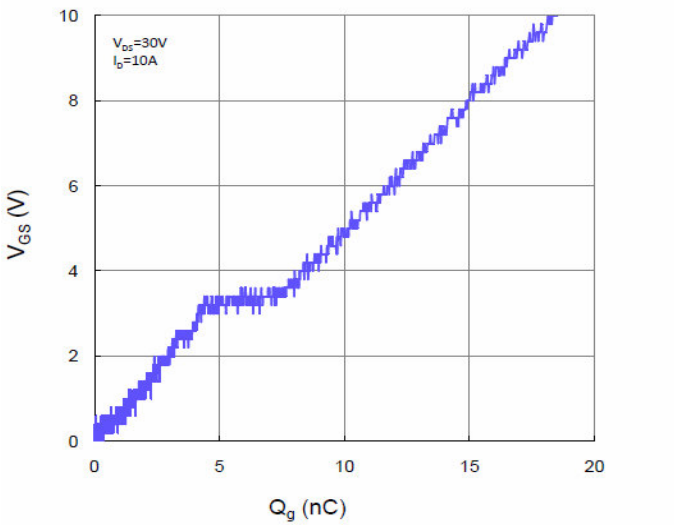


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

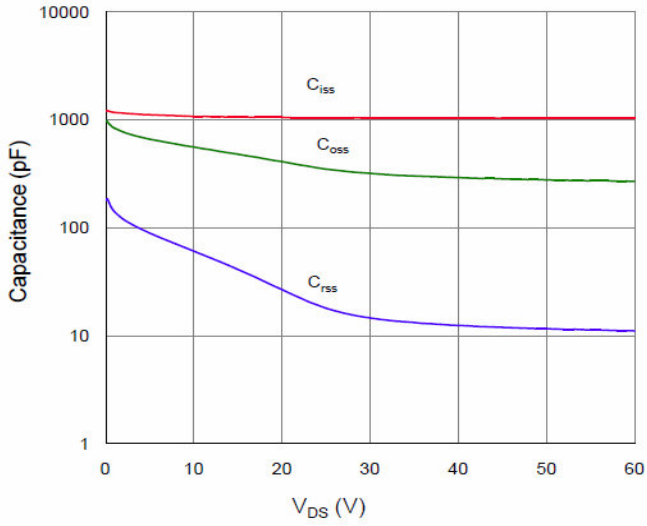


Figure 9. Maximum Safe Operating Area

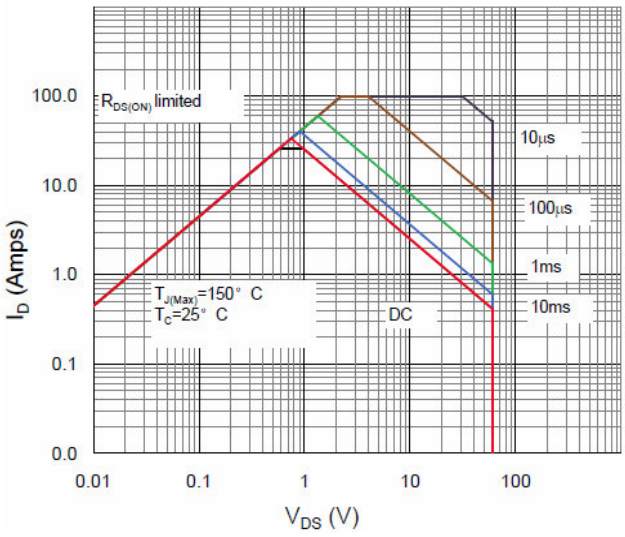


Figure 10. Maximun Drain Current vs. Case Temperature

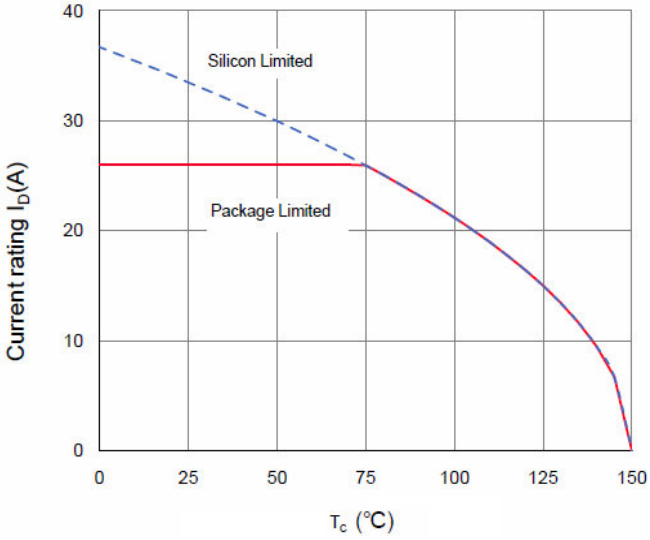


Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Case